



WEST - [resubmit.wsp.1]

File View Edit Tools Window Help

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Drafts  
Pending  
Active

L1: (7673) (control adj gate).clm.  
L2: (2395) 1 and (sidewall\$1 or spacer\$1)  
L3: (1732) 2 and ((non adj volatile) or nonvolatile)  
L4: (1731) 3 and memory  
L5: (132) 4 and ((multi adj bit\$1) or (buried adj bit\$1))  
L6: (1052) 4 and (bitline\$1 or (bit\$1 adj line\$1))  
L7: (510) 6 and (spacer\$1 or sidewall\$1).clm.  
L8: (186) 7 and buried  
L9: (52) 8 and (buried near (bit\$1 or bitline\$1 or (bit adj line\$1)))  
L10: (39) 9 and ((charge adj storage) or ONO or (oxide adj nitride adj oxid  
Failed

SPACER LEAT  
Default generator OR  
8 and (buried near (bit\$1 or bitline\$1 or (bit adj line\$1)))

	U	I	P	T	P	Document ID	Issue Date	Pages	Title	Current OR	Current NR	Retrieval	Inventor	S	C				
29						US 6476439	20021105	24	Double-bit non-volatile	257/315	257/316		Chen, Chin-Yang	P					
						B2			memory structure and co		257/321								
30						US 6372564	20020416	9	Method of manufacturing	438/192	257/E29.30		Lee, Robin	P					
						B1			V-shaped flash memory		6								
31						US 6211548	20010403	18	Metal-gate non-volatile	257/321	257/324		Ma, Yueh Yale	P					
						B1			memory cell		257/649								
32						US 6143636	20001107	26	High density flash	438/587	257/315		Forbes, Leonard et al.	P					
						A			memory		257/319								
33						US 6084265	20000704	8	High density shallow	257/332	257/314		Wu, Shye-Lin	P					
						A			trench contactless nonv		257/321								
34						US 5963808	19991005	23	Method of forming an	438/286	257/E21.68		Liu, Wenpin et al.	P					
						A			asymmetric bird's beak		2								
35						US 5960285	19990928	8	Flash EEPROM device	438/264	257/321		Hong, Gary	P					
						A					257/E21.42								
36						US 5936889	19990810	18	Array of nonvolatile	365/185.22	365/185.14		Choi, Woong-Lim	P					
						A			memory devices and methn										
37						US 5880499	19990309	11	Memory cell of a	257/316	257/315		Oyama, Ken-Ichi	P					
						A			nonvolatile semiconduct		257/317								
38						US 5837584	19981117	15	Virtual ground flash	438/263	257/E21.68		Liu, Wenpin et al.	P					
						A			cell with asymmetrical		2								
39						US 5768186	19980616	17	High density single	365/185.01	257/E21.68		Ma, Yueh Yale	P					
						A			polv metal-gate non-vol		8								
40						US 5707897	19980113	12	Non-volatile-memory	438/257	257/E21.68		Lee, Jin-Yuan et al.	P					
						A			cell for electrically p		2								
41						US 5703387	19971230	8	Split gate memory cell	257/315	257/321		Hong, Gary	P					
						A			with vertical floating		257/E21.69								
42						US 5656840	19970812	16	Single bit erase flash	257/316	257/319		Yang, Ming-Tzong	P					
						A			EEPROM		257/321								
43						US 5635415	19970603	14	Method of manufacturing	438/261	257/E21.68		Hong, Gary	P					
						A			buried bit line flash E		2								
44						US 5238855	19930824	10	Cross-point	438/261	257/E27.10		Gill, Manzur	P					
						A			contact-free array with		3								

U No. I Date. R. Date.

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